

TECHNICAL DATA
DATA SHEET 4766, REV. A

HERMETIC SCHOTTKY RECTIFIER
Very Low Forward Voltage Drop

Features:

- Soft Reverse Recovery at Low and High Temperature
- Very Low Forward Voltage Drop
- Low Power Loss, High Efficiency
- High Surge Capacity
- Guard Ring for Enhanced Durability and Long Term Reliability
- Guaranteed Reverse Avalanche Characteristics

Maximum Ratings

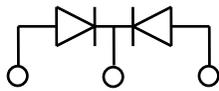
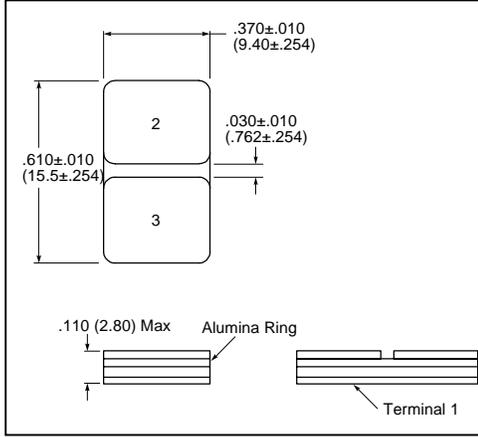
Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V_{RWM}	-	60	V
Max. Average Forward Current	$I_{F(AV)}$	50% duty cycle, rectangular wave form (Single)	60	A
Max. Average Forward Current	$I_{F(AV)}$	50% duty cycle, rectangular wave form (Common Cathode)	120	A
Max. Peak One Cycle Non-Repetitive Surge Current	I_{FSM}	8.3 ms, half Sine wave (per leg)	860	A
Non-Repetitive Avalanche Energy	E_{AS}	$T_J = 25\text{ }^\circ\text{C}$, $I_{AS} = 3.0\text{ A}$, $L = 4.4\text{ mH}$ (per leg)	20	mJ
Repetitive Avalanche Current	I_{AR}	I_{AS} decay linearly to 0 in 1 μs f limited by T_J max $V_A=1.5V_R$	3.0	A
Maximum Thermal Resistance	$R_{\theta JC}$	DC operation	0.18	$^\circ\text{C/W}$
Max. Junction Temperature	T_J	-	-65 to +175	$^\circ\text{C}$
Max. Storage Temperature	T_{stg}	-	-65 to +175	$^\circ\text{C}$

Electrical Characteristics

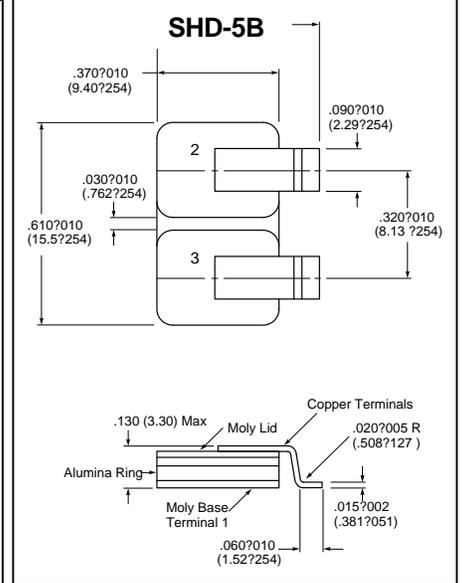
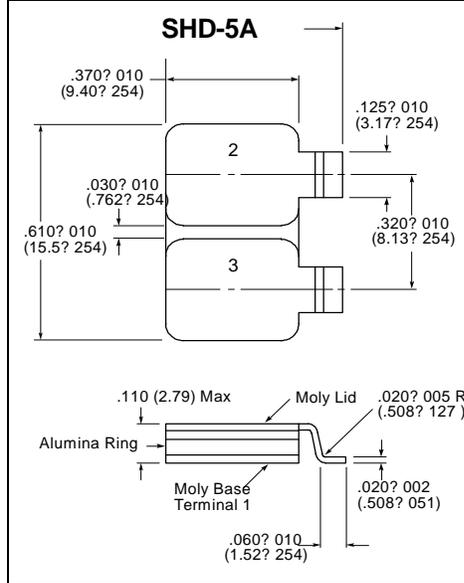
Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop (per leg)	V_{F1}	@ 60A, Pulse, $T_J = 25\text{ }^\circ\text{C}$	0.66	V
	V_{F2}	@ 60A, Pulse, $T_J = 125\text{ }^\circ\text{C}$	0.59	V
Max. Reverse Current (per leg)	I_{R1}	@ $V_R = 60\text{V}$, Pulse, $T_J = 25\text{ }^\circ\text{C}$	1.2	mA
	I_{R2}	@ $V_R = 60\text{V}$, Pulse, $T_J = 125\text{ }^\circ\text{C}$	90	mA
Max. Junction Capacitance (per leg)	C_T	@ $V_R = 5\text{V}$, $T_C = 25\text{ }^\circ\text{C}$ $f_{SIG} = 1\text{MHz}$, $V_{SIG} = 50\text{mV}$ (p-p)	2600	pF

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MECHANICAL DIMENSIONS: In Inches / mm



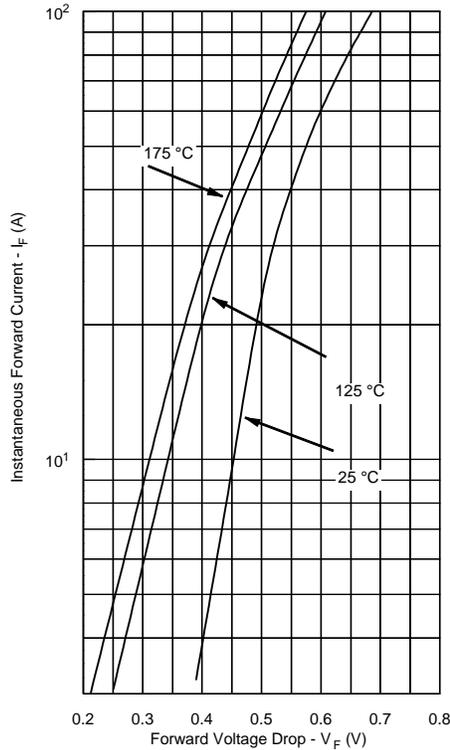
1 2 3
PINOUT TABLE



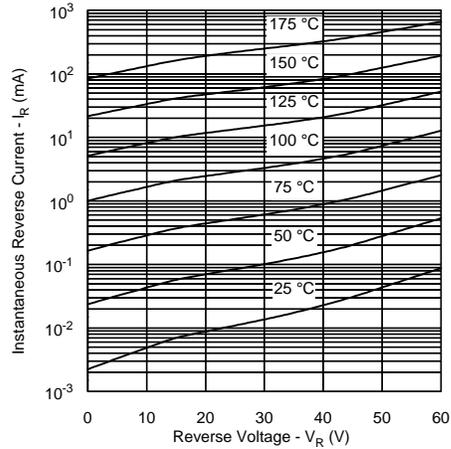
DEVICE TYPE	PIN 1	PIN 2	PIN 3
DUAL RECTIFIER, COMMON CATHODE (P)	COMMON CATHODE	ANODE	ANODE

Note: The V_f curves shown are for the SD200SB60 unpackaged die only.

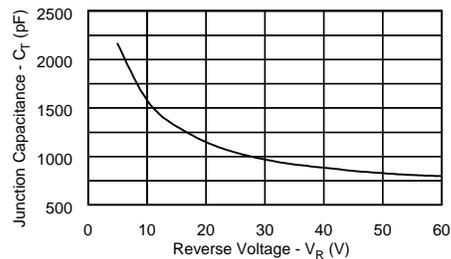
Typical Forward Characteristics



Typical Reverse Characteristics



Typical Junction Capacitance



TECHNICAL DATA

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